NCV8401

Self-Protected Low Side Driver with Temperature and Current Limit

NCV8401 is a three terminal protected Low-Side Smart Discrete device. The protection features include overcurrent, overtemperature, ESD and integrated Drain-to-Gate clamping for overvoltage protection. This device offers protection and is suitable for harsh automotive environments.

Features

- Short Circuit Protection
- Thermal Shutdown with Automatic Restart
- Over Voltage Protection
- Integrated Clamp for Inductive Switching
- ESD Protection
- dV/dt Robustness
- Analog Drive Capability (Logic Level Input)
- RoHs Compliant
- AEC-Q101 Qualified
- NCV Prefix for Automotive and Other Applications Requiring Site and Change Control
- This is a Pb−Free Device

Typical Applications

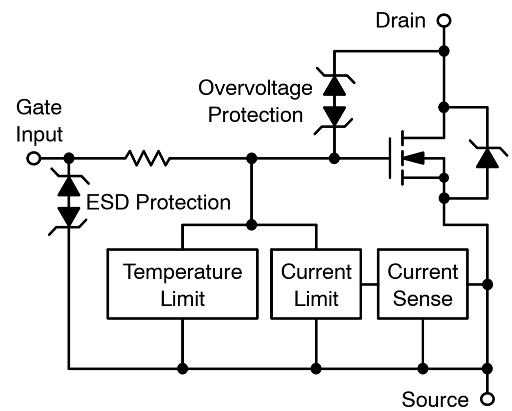
- Switch a Variety of Resistive, Inductive and Capacitive Loads
- Can Replace Electromechanical Relays and Discrete Circuits
- Automotive / Industrial

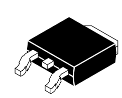
ON Semiconductor®

http://onsemi.com

V_{DSS} (Clamped)	$R_{DS(ON)}$ TYP	I_D MAX (Limited)
42 V	23 mΩ @ 10 V	33 A*

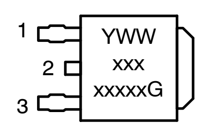
*Max current may be limited below this value depending on input conditions.





DPAK CASE 369C STYLE 2

MARKING DIAGRAM



Y	= Year		
WW	= Work Week	1	= Gate
xxx	= Device Code	2	= Drain
G	= Pb−Free Package	3	= Source

ORDERING INFORMATION

Device	Package	Shipping†
NCV8401DTRKG	DPAK (Pb−Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain−to−Source Voltage Internally Clamped	V_{DSS}	42	V
Drain−to−Gate Voltage Internally Clamped (R_{GS} = 1.0 MΩ)	V_{DGR}	42	V
Gate−to−Source Voltage	V_{GS}	±14	V
Drain Current − Continuous	I_D	Internally Limited	
Total Power Dissipation @ T_A = 25°C (Note 1) @ T_A = 25°C (Note 2)	P_D	 1.1 2.0	W
Thermal Resistance, Junction−to−Case Junction−to−Ambient (Note 1) Junction−to−Ambient (Note 2)	$R_{\theta JC}$ $R_{\theta JA}$ $R_{\theta JA}$	1.6 110 60	°C/W
Single Pulse Drain−to−Source Avalanche Energy (V_{DD} = 25 Vdc, V_{GS} = 5.0 Vdc, I_L = 3.65 Apk, L = 120 mH, R_G = 25 Ω, T_{Jstart} = 150°C) (Note 3)	E_{AS}	800	mJ
Load Dump Voltage (V_{GS} = 0 and 10 V, R_I = 2.0 Ω, R_L = 3.0 Ω, t_d = 400 ms)	V_{LD}	65	V
Operating Junction Temperature	T_J	−40 to 150	°C
Storage Temperature	T_{stg}	−55 to 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Minimum FR4 PCB, steady state.
2. Mounted onto a 2″ square FR4 board (1″ square, 2 oz. Cu 0.06″ thick single−sided, t = steady state).
3. Not subject to production testing.

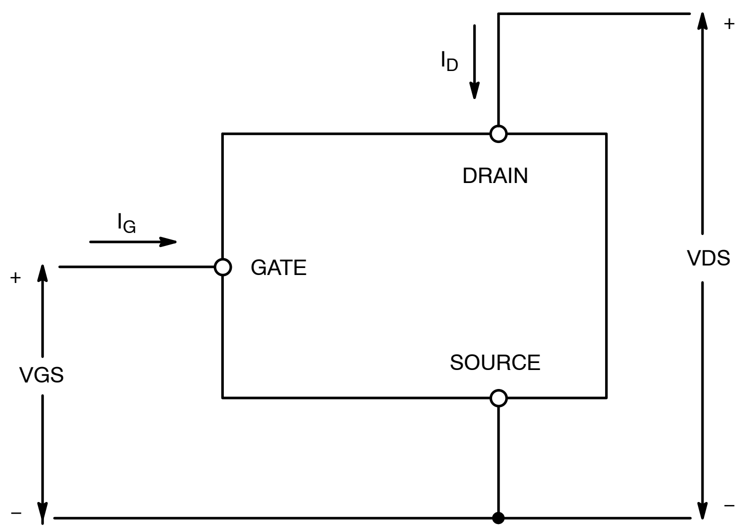


Figure 1. Voltage and Current Convention

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

OFF CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Drain−to−Source Clamped Breakdown Voltage (V_{GS} = 0 Vdc, I_D = 250 μAdc) (V_{GS} = 0 Vdc, I_D = 250 μAdc, T_J = 150°C) (Note 4)	$V_{(BR)DSS}$	 42 42	 46 44	 50 50	Vdc
Zero Gate Voltage Drain Current (V_{DS} = 32 Vdc, V_{GS} = 0 Vdc) (V_{DS} = 32 Vdc, V_{GS} = 0 Vdc, T_J = 150°C) (Note 4)	I_{DSS}		 1.5 6.5	 5.0	μAdc
Gate Input Current (V_{GS} = 5.0 Vdc, V_{DS} = 0 Vdc)	I_{GSSF}		50	100	μAdc

ON CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.2 mAdc) Threshold Temperature Coefficient	$V_{GS(th)}$	 1.0	 1.8 5.0	 2.0	 Vdc −mV/°C
Static Drain−to−Source On−Resistance (Note 5) (V_{GS} = 10 Vdc, I_D = 5.0 Adc, T_J @ 25°C) (V_{GS} = 10 Vdc, I_D = 5.0 Adc, T_J @ 150°C) (Note 4)	$R_{DS(on)}$		 23 43	 29 55	mΩ
Static Drain−to−Source On−Resistance (Note 5) (V_{GS} = 5.0 Vdc, I_D = 5.0 Adc, T_J @ 25°C) (V_{GS} = 5.0 Vdc, I_D = 5.0 Adc, T_J @ 150°C) (Note 4)	$R_{DS(on)}$		 28 50	 34 60	mΩ
Source−Drain Forward On Voltage (I_S = 5 A, V_{GS} = 0 V)	V_{SD}		0.80	1.1	V

SWITCHING CHARACTERISTICS (Note 4)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Turn−ON Time (10% V_{IN} to 90% I_D)	V_{IN} = 0 V to 5 V, V_{DD} = 25 V I_D = 1.0 A, Ext R_G = 2.5 Ω	t_{ON}		41	50	μs
Turn−OFF Time (90% V_{IN} to 10% I_D)		t_{OFF}		129	150	
Turn−ON Time (10% V_{IN} to 90% I_D)	V_{IN} = 0 V to 10 V, V_{DD} = 25 V, I_D = 1.0 A, Ext R_G = 2.5 Ω	t_{ON}		16	25	
Turn−OFF Time (90% V_{IN} to 10% I_D)		t_{OFF}		164	180	
Slew−Rate ON (20% V_{DS} to 50% V_{DS})	V_{in} = 0 to 10 V, V_{DD} = 12 V, R_L = 4.7 Ω	$-dV_{DS}/dt_{ON}$		1.27		V/μs
Slew−Rate OFF (80% V_{DS} to 50% V_{DS})		dV_{DS}/dt_{OFF}		0.36		

SELF PROTECTION CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Current Limit	V_{GS} = 5.0 V, V_{DS} = 10 V V_{GS} = 5.0 V, T_J = 150°C (Note 4)	I_{LIM}	25 11	30 16	35 21	Adc
	V_{GS} = 10 V, V_{DS} = 10 V V_{GS} = 10 V, T_J = 150°C (Note 4)		30 18	35 25	40 28	
Temperature Limit (Turn−off)	V_{GS} = 5.0 V (Note 4)	$T_{LIM(off)}$	150	175	200	°C
Thermal Hysteresis	V_{GS} = 5.0 V	$\Delta T_{LIM(on)}$		15		°C
Temperature Limit (Turn−off)	V_{GS} = 10 V (Note 4)	$T_{LIM(off)}$	150	165	185	°C
Thermal Hysteresis	V_{GS} = 10 V	$\Delta T_{LIM(on)}$		15		°C

GATE INPUT CHARACTERISTICS (Note 4)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Device ON Gate Input Current	V_{GS} = 5 V I_D = 1.0 A	I_{GON}		50		μA
	V_{GS} = 10 V I_D = 1.0 A			400		
Current Limit Gate Input Current	V_{GS} = 5 V, V_{DS} = 10 V	I_{GCL}		0.1		mA
	V_{GS} = 10 V, V_{DS} = 10 V			0.7		
Thermal Limit Fault Gate Input Current	V_{GS} = 5 V, V_{DS} = 10 V	I_{GTL}		0.6		mA
	V_{GS} = 10 V, V_{DS} = 10 V			2.0		

ESD ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (Note 4)

Characteristic	Symbol	Min	Typ	Max	Unit
Electro−Static Discharge Capability Human Body Model (HBM) Machine Model (MM)	ESD	 4000 400			V

4. Not subject to production testing.
5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

TYPICAL PERFORMANCE CURVES

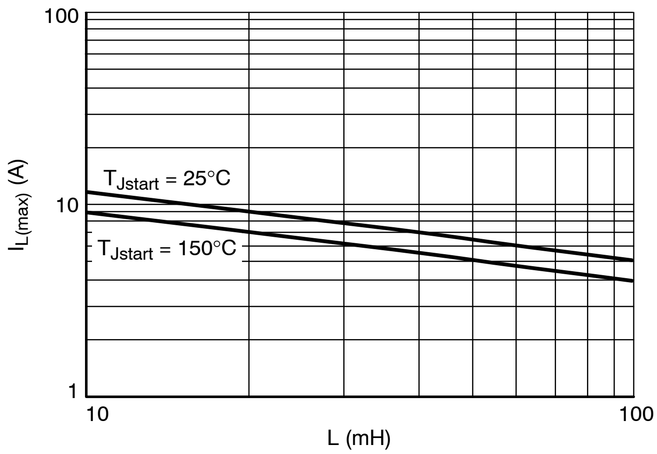


Figure 2. Single Pulse Maximum Switch−off Current vs. Load Inductance

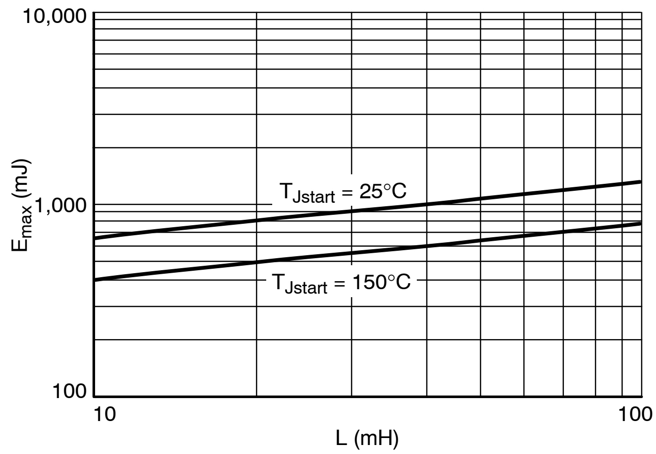


Figure 3. Single Pulse Maximum Switching Energy vs. Load Inductance

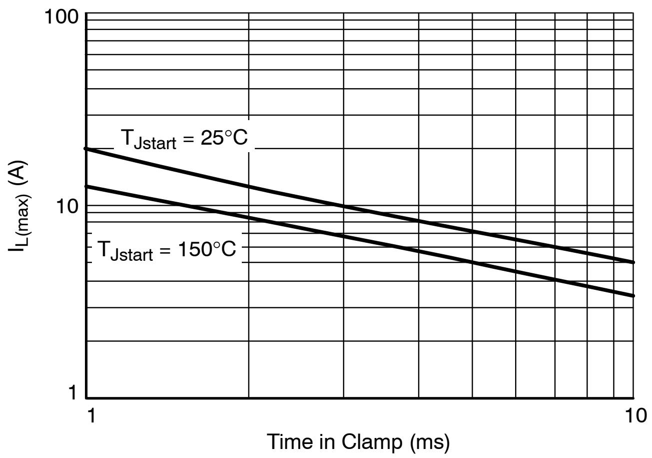


Figure 4. Single Pulse Maximum Inductive Switch−off Current vs. Time in Clamp

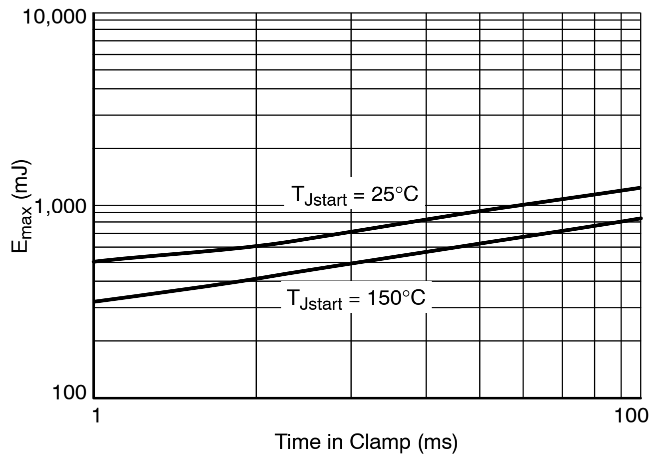


Figure 5. Single Pulse Maximum Inductive Switching Energy vs. Time in Clamp

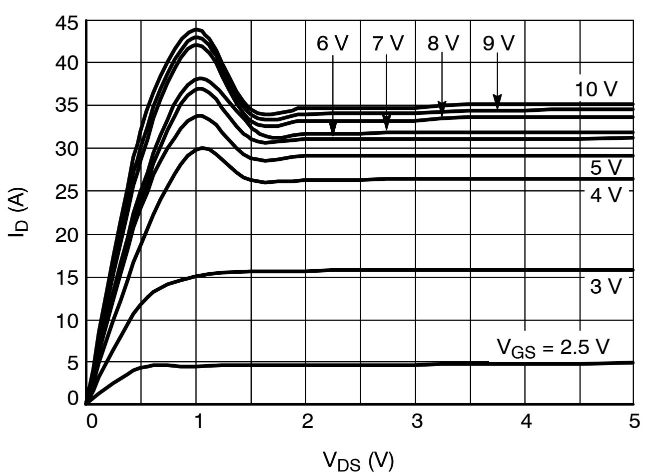


Figure 6. On−state Output Characteristics at 25°C

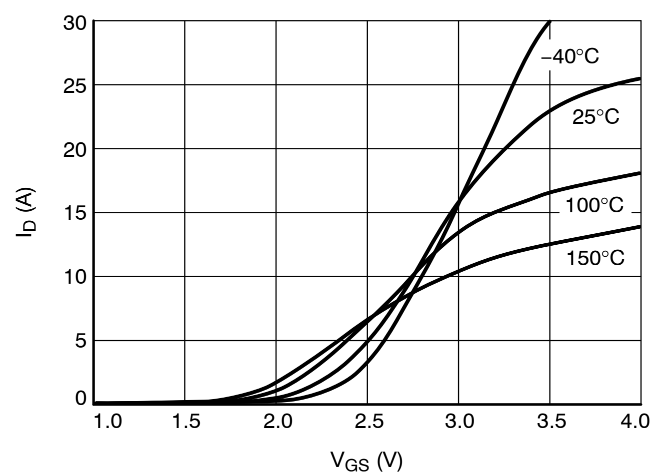


Figure 7. Transfer Characteristics (V_{DS} = 10 V)

TYPICAL PERFORMANCE CURVES

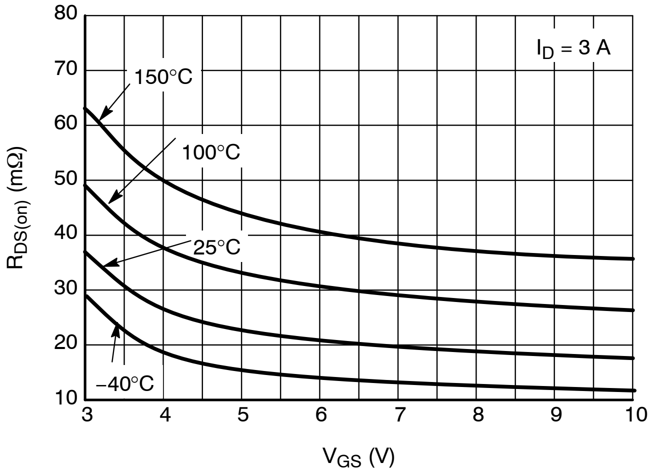


Figure 8. $R_{DS(on)}$ vs. Gate−Source Voltage

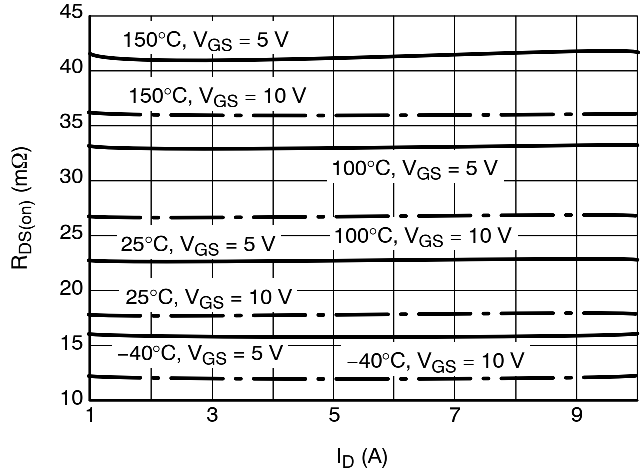


Figure 9. $R_{DS(on)}$ vs. Drain Current

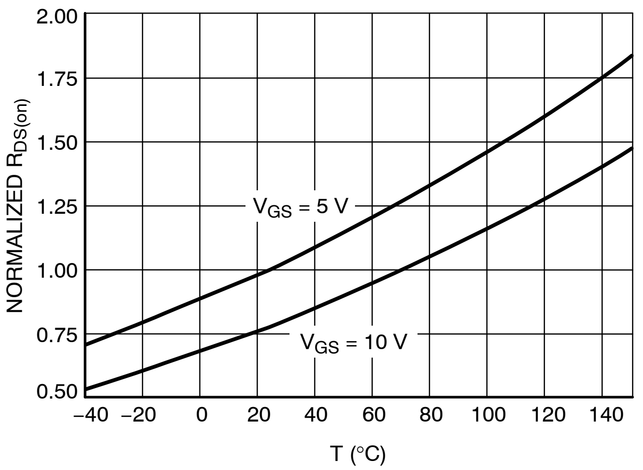


Figure 10. Normalized $R_{DS(on)}$ vs. Temperature (I_D = 5 A)

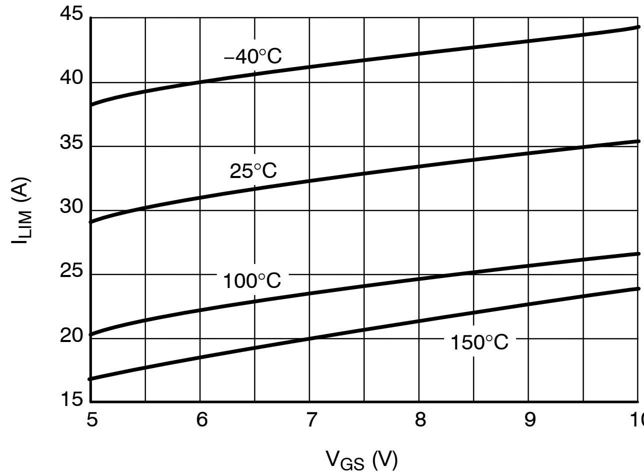


Figure 11. Current Limit vs. Gate−Source Voltage (V_{DS} = 10 V)

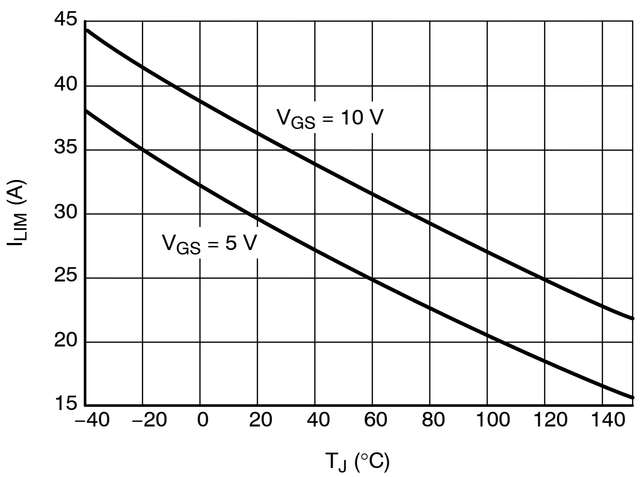


Figure 12. Current Limit vs. Junction Temperature (V_{DS} = 10 V)

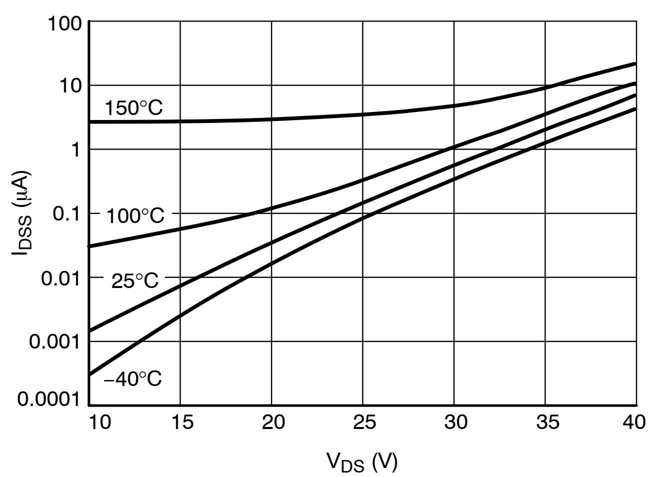


Figure 13. Drain−to−Source Leakage Current (V_{GS} = 0 V)

TYPICAL PERFORMANCE CURVES

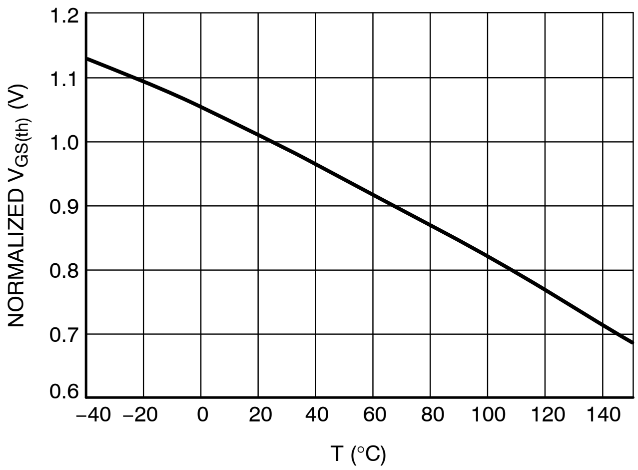


Figure 14. Normalized Threshold Voltage vs. Temperature (I_D = 1.2 mA, V_{DS} = V_{GS})

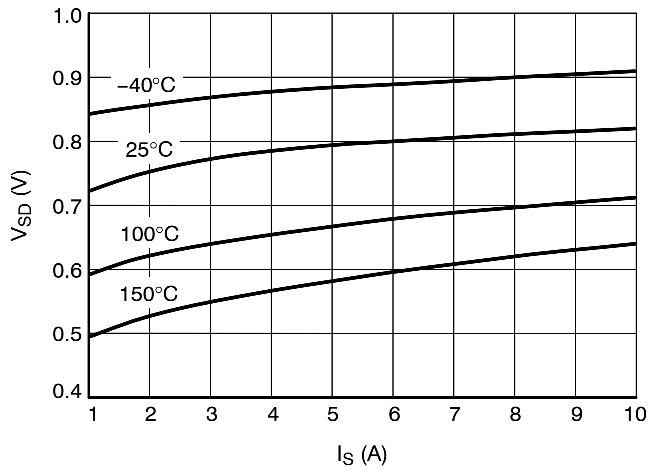


Figure 15. Source−Drain Diode Forward Characteristics (V_{GS} = 0 V)

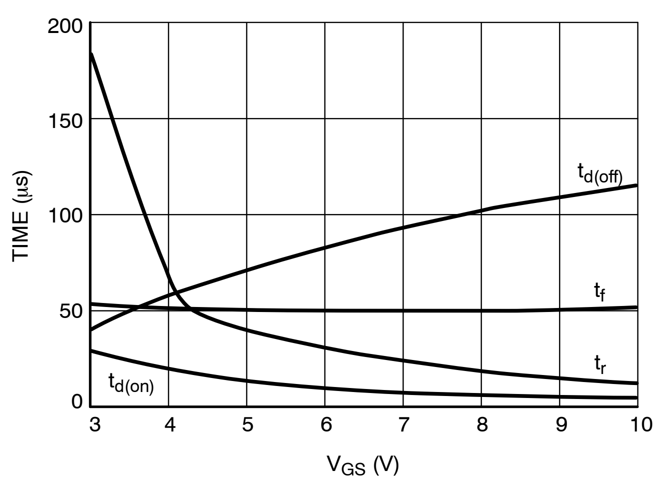


Figure 16. Resistive Load Switching Time vs. Gate−Source Voltage (V_{DD} = 25 V, I_D = 5 A, R_G = 0 Ω)

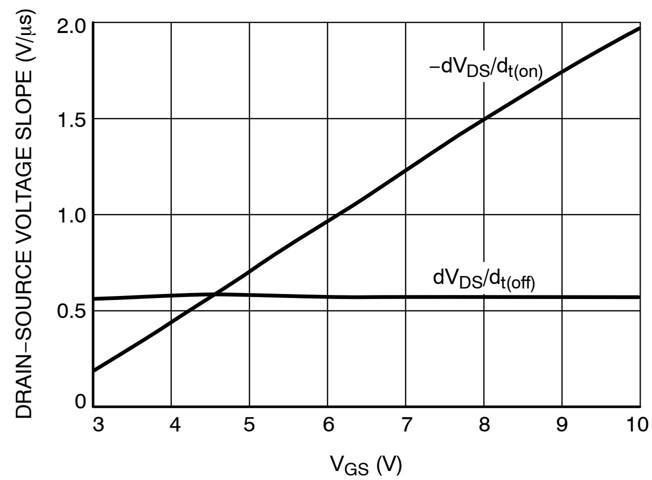


Figure 17. Resistive Load Switching Drain−Source Voltage Slope vs. Gate−Source Voltage (V_{DD} = 25 V, I_D = 5 A, R_G = 0 Ω)

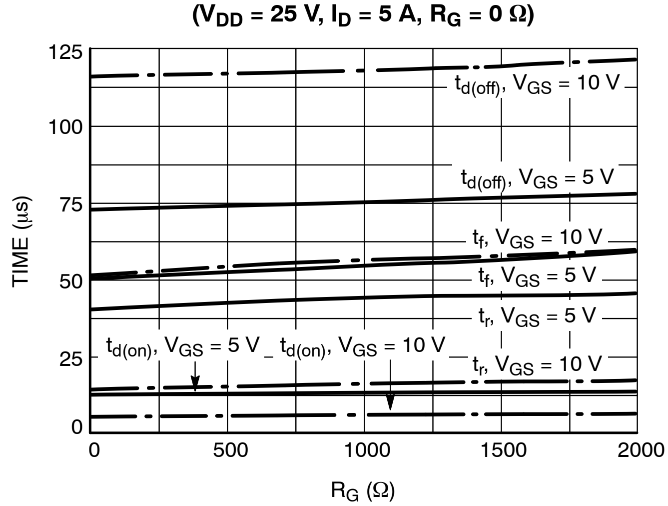


Figure 18. Resistive Load Switching Time vs. Gate Resistance (V_{DD} = 25 V, I_D = 5 A)

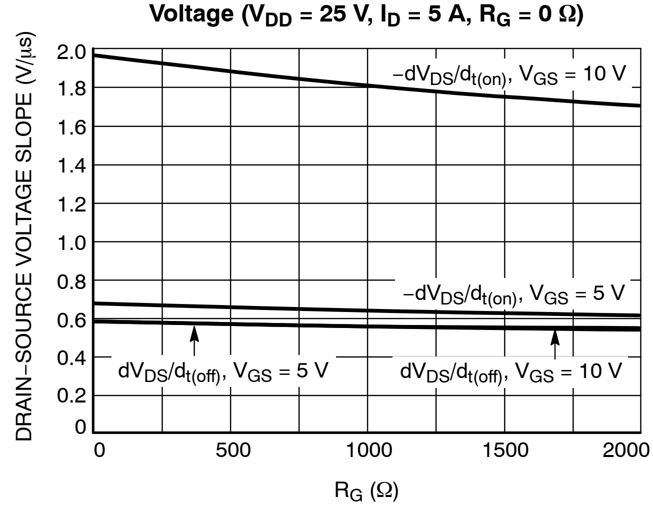


Figure 19. Drain−Source Voltage Slope during Turn On and Turn Off vs. Gate Resistance (V_{DD} = 25 V, I_D = 5 A)

TYPICAL PERFORMANCE CURVES

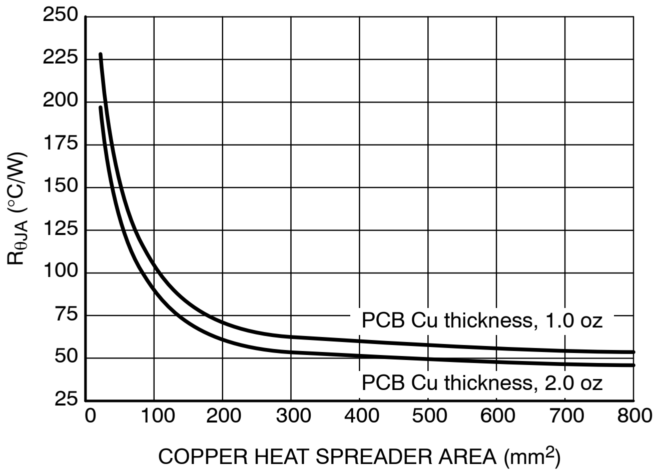


Figure 20. $R_{\theta JA}$ vs. Copper Area

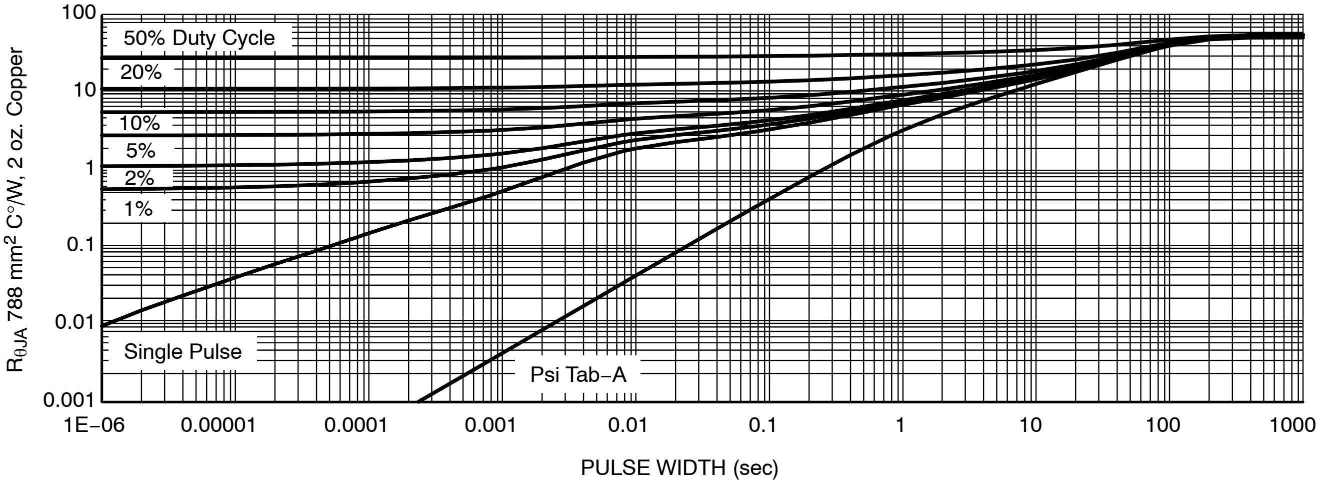


Figure 21. Transient Thermal Resistance

TEST CIRCUITS AND WAVEFORMS

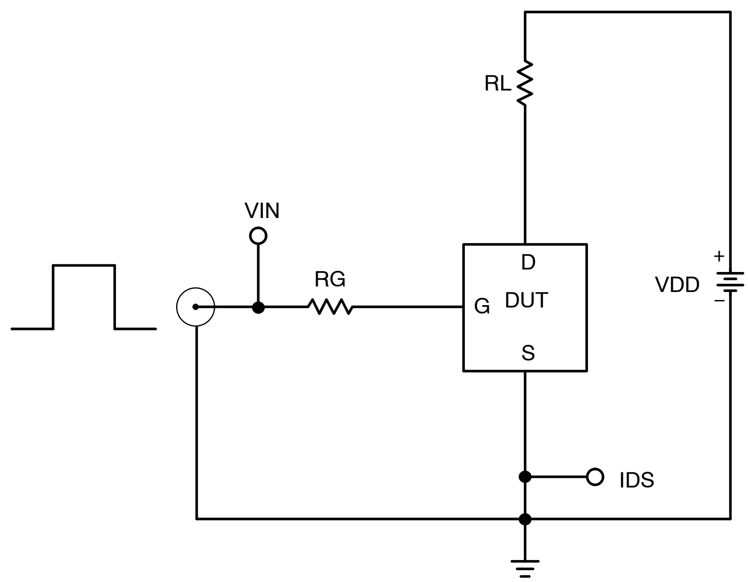


Figure 22. Resistive Load Switching Test Circuit

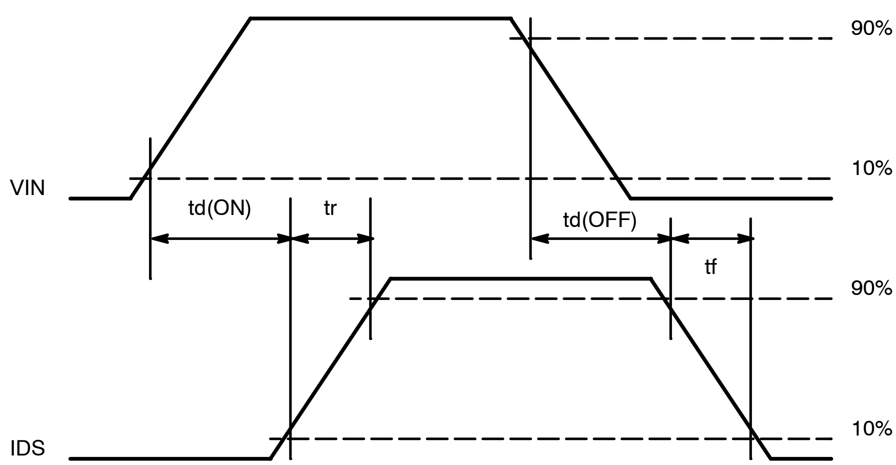


Figure 23. Resistive Load Switching Waveforms

TEST CIRCUITS AND WAVEFORMS

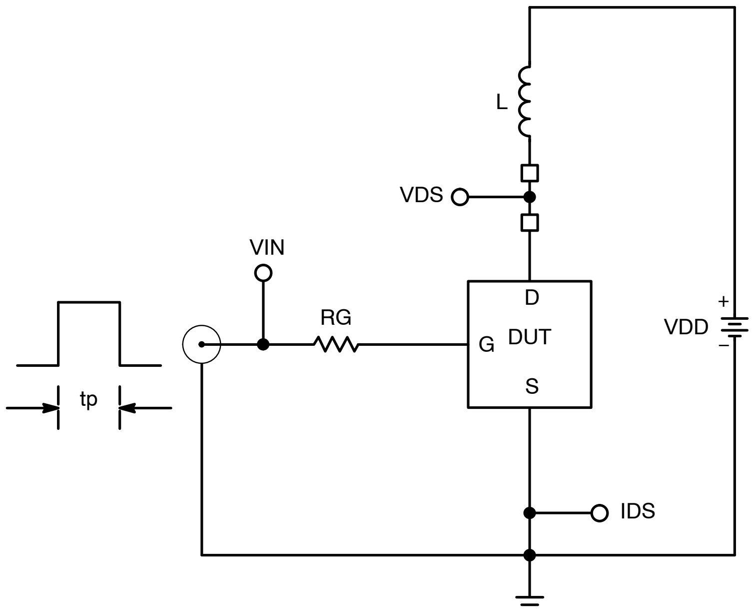


Figure 24. Inductive Load Switching Test Circuit

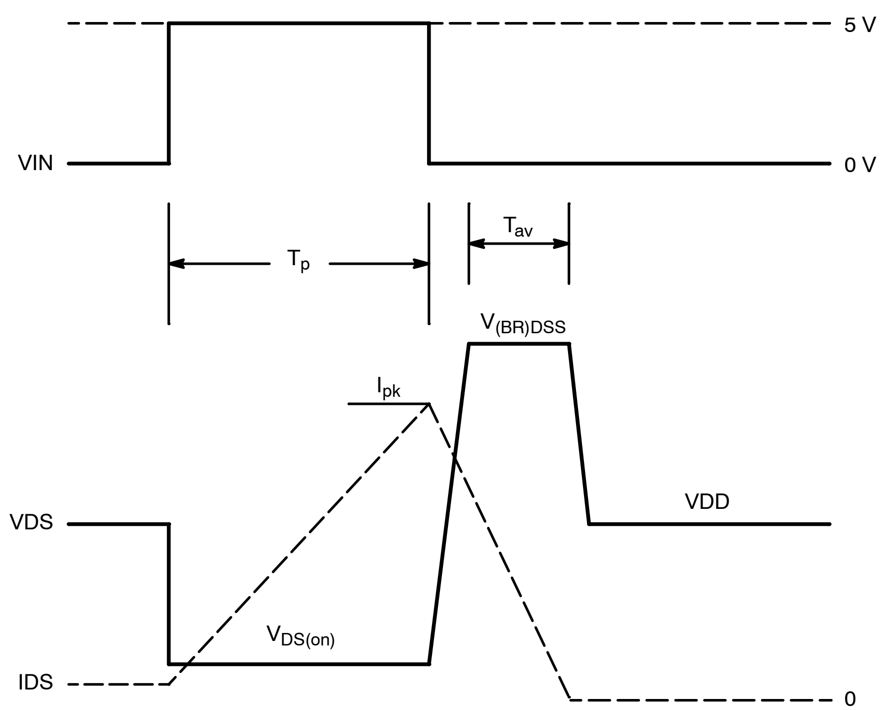
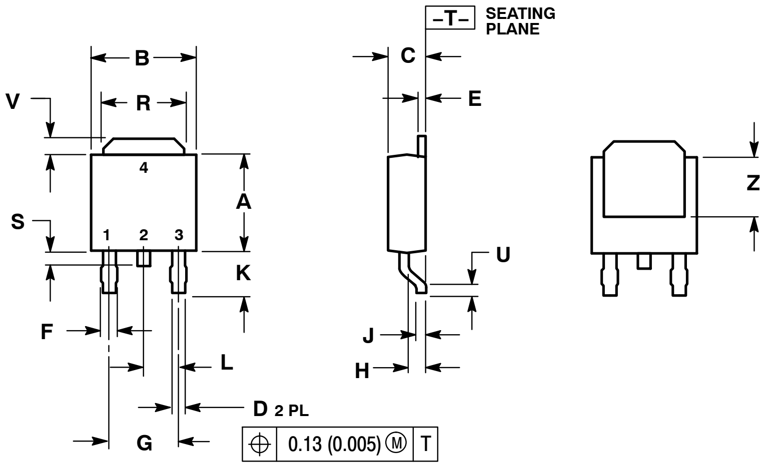


Figure 25. Inductive Load Switching Waveforms

PACKAGE DIMENSIONS

DPAK
CASE 369C−01
ISSUE O

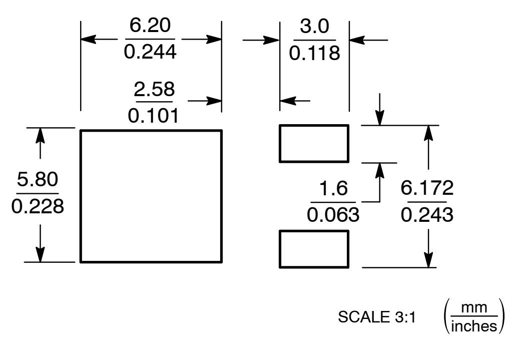


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020	−−−	0.51	−−−
V	0.035	0.050	0.89	1.27
Z	0.155	−−−	3.93	−−−

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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